

MOSFETs Silicon N-channel MOS (U-MOSIX-H)

# TPH2R506PL

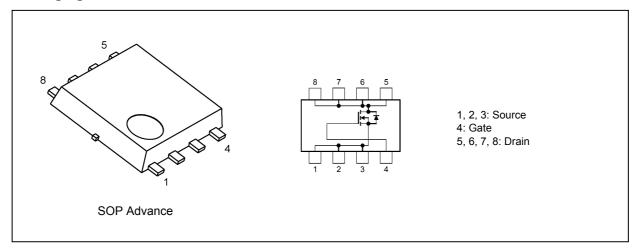
#### 1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- · Motor Drivers

#### 2. Features

- (1) High-speed switching
- (2) Small gate charge :  $Q_{SW} = 19 \text{ nC (typ.)}$
- (3) Small output charge :  $Q_{oss} = 51 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance :  $R_{DS(ON)} = 1.9 \text{ m}\Omega \text{ (typ.)}(V_{GS} = 10 \text{ V})$
- (5) Low leakage current :  $I_{DSS} = 10 \mu A (max)(V_{DS} = 60 V)$
- (6) Enhancement mode :  $V_{th}$  = 1.5 to 2.5 V ( $V_{DS}$  = 10 V,  $I_{D}$  = 0.5 mA)

#### 3. Packaging and Internal Circuit



1



## 4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			$V_{DSS}$	60	V
Gate-source voltage			$V_{GSS}$	±20	
Drain current (DC)	( T <sub>c</sub> = 25 °C )	(Note 1)	Ι <sub>D</sub>	100	Α
Drain current (DC)	( Silicon limit )	(Note 1), (Note 2)	$I_D$	160	
Drain current (pulsed)	( t = 100 μs )	(Note 1)	I <sub>DP</sub>	500	
Power dissipation	( T <sub>c</sub> = 25 °C )		$P_{D}$	132	W
Power dissipation		(Note 3)	$P_{D}$	3.0	
Power dissipation		(Note 4)	$P_{D}$	0.96	
Single-pulse avalanche energy		(Note 5)	E <sub>AS</sub>	65	mJ
Single-pulse avalanche current		(Note 5)	I <sub>AS</sub>	100	Α
Channel temperature			T <sub>ch</sub>	175	°C
Storage temperature			T <sub>stg</sub>	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal resistance	$(T_c = 25 ^{\circ}C)$		R <sub>th(ch-c)</sub>	1.13	°C/W
Channel-to-ambient thermal resistance	( T <sub>a</sub> = 25 °C )	(Note 3)	R <sub>th(ch-a)</sub>	50	
Channel-to-ambient thermal resistance	( T <sub>a</sub> = 25 °C )	(Note 4)	R <sub>th(ch-a)</sub>	156	

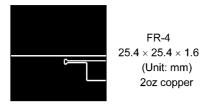
Note 1: Ensure that the channel temperature does not exceed 175 °C.

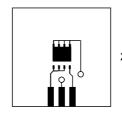
Note 2: Limited by silicon chip capability.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5:  $V_{DD}$  = 48 V,  $T_{ch}$  = 25 °C (initial), L = 5  $\mu$ H,  $I_{AS}$  = 100 A





FR-4  $25.4 \times 25.4 \times 1.6$  (Unit: mm) 2oz copper

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

## 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	μΑ
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	60			٧
Drain-source breakdown voltage (Note 6)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	45	_	_	
Gate threshold voltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.5 mA	1.5	_	2.5	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 30 A	_	2.8	4.4	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 50 A	_	1.9	2.5	

Note 6: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V,	_	4180	5435	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	60	115	
Output capacitance	C <sub>oss</sub>		_	770	_	
Gate resistance	r <sub>g</sub>	_	_	0.6	1.1	Ω
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1	_	7.1	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	16	_	
Switching time (fall time)	t <sub>f</sub>		_	13	_	
Switching time (turn-off time)	t <sub>off</sub>		_	39	_	

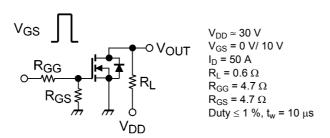


Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$	_	60		nC
		$V_{DD} \approx 30 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 50 \text{ A}$	_	32	1	
Gate-source charge 1	Q <sub>gs1</sub>	$V_{DD} \approx 30 \text{ V}, V_{GS} = 10 \text{ V},$	_	17	_	
Gate-drain charge	$Q_{gd}$	I <sub>D</sub> = 50 A	_	11	_	
Gate switch charge	$Q_{SW}$		_	19	_	
Output charge	Q <sub>oss</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	51		



## 6.4. Source-Drain Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 7)	I <sub>DRP</sub>	(t = 100 μs)	_	_	500	Α
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 100 A, V <sub>GS</sub> = 0 V	_	_	-1.2	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 25 A, V <sub>GS</sub> = 0 V,	_	49	_	ns
Reverse recovery charge	$Q_{rr}$	-dI <sub>DR</sub> /dt = 100 A/μs	_	57		nC

Note 7: Ensure that the channel temperature does not exceed 175  $^{\circ}\text{C}$ .

## 7. Marking

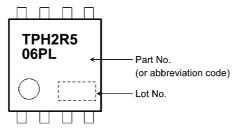


Fig. 7.1 Marking

#### 8. Characteristics Curves (Note)

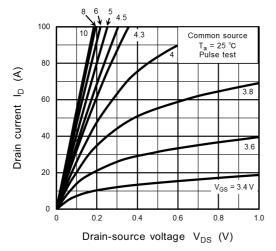


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

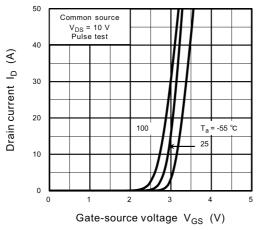


Fig. 8.3 I<sub>D</sub> - V<sub>GS</sub>

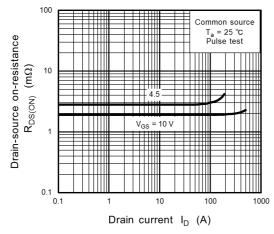


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

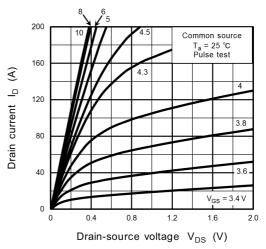
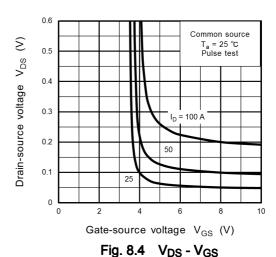


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>



0 20 00

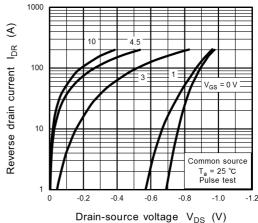


Fig. 8.6 I<sub>DR</sub> - V<sub>DS</sub>

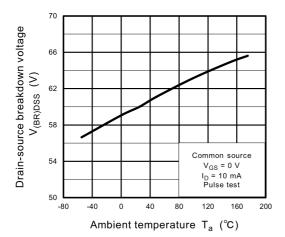


Fig. 8.7 V<sub>(BR)DSS</sub> - T<sub>a</sub>

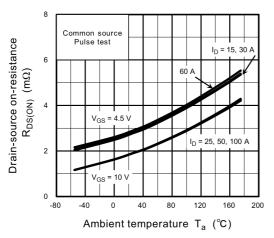


Fig. 8.9 R<sub>DS(ON)</sub> - T<sub>a</sub>

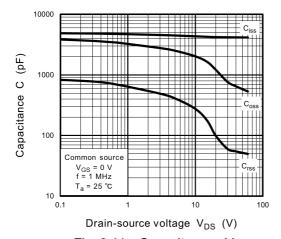


Fig. 8.11 Capacitance - V<sub>DS</sub>

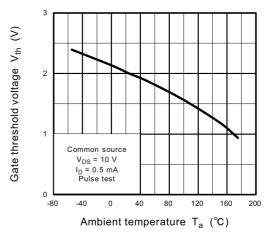


Fig. 8.8 V<sub>th</sub> - T<sub>a</sub>

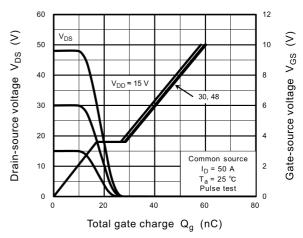


Fig. 8.10 Dynamic Input/Output Characteristics

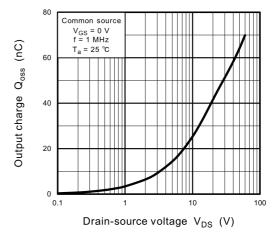


Fig. 8.12 Q<sub>oss</sub> - V<sub>DS</sub>

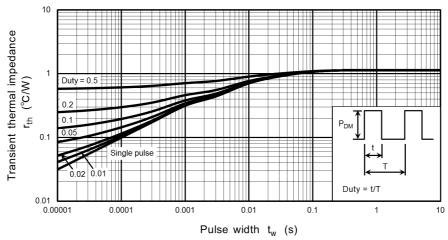


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

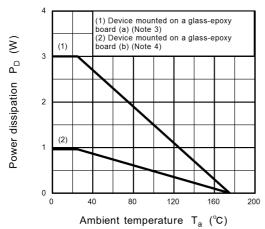


Fig. 8.14 P<sub>D</sub> - T<sub>a</sub> (Guaranteed Maximum)

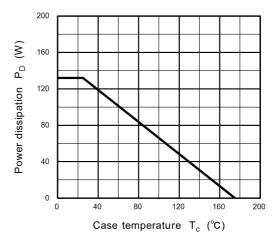
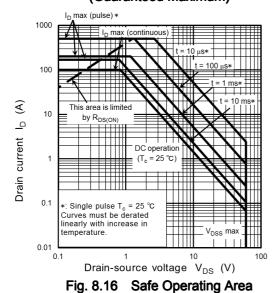


Fig. 8.15 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)



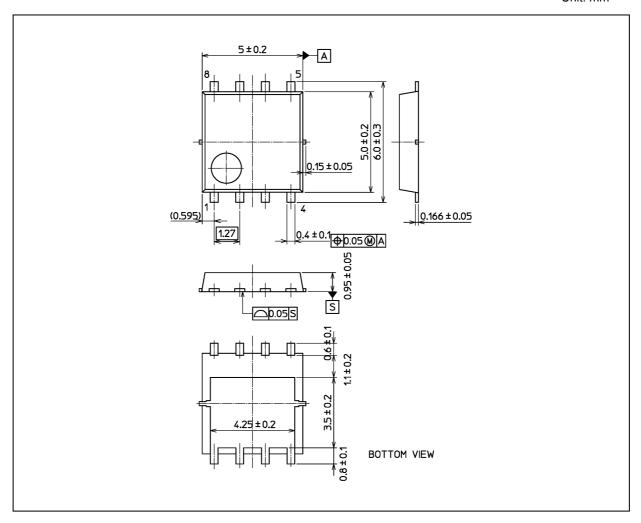
(Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 0.069 g (typ.)

Pa	ackage Name(s)
TOSHIBA: 2-5Q1S	
Nickname: SOP Advance	



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